

Application of: Euijoon Yoon et al.
Serial No.: 10/596,126
Amendment after Non-Final Office Action

AMENDMENTS TO THE ABSTRACT

Please replace the original Abstract with the following paragraph:

[Abstract]

~~The present invention relates to a growth method of nitride semiconductor layer~~
~~comprising a first step for growing~~ Growing ~~a first nitride~~ a first nitride ~~[[5]] semiconductor layer on an~~
 ~~$\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ ($0 < x < 1, 0 < y < 1, 0 < x+y < 1$) $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ ($0 \leq x \leq 1, 0 \leq y \leq 1, 0 < x+y \leq 1$) layer, a~~
~~second step for reducing the thickness of the first nitride semiconductor layer by growth~~
~~interruption and, a third step for growing a second nitride semiconductor layer having a band gap~~
~~energy higher than that of the first nitride semiconductor layer on the first nitride semiconductor~~
~~layer with the [[to]] reduced thickness and a light emitting device using the growth method.~~